

R-C Thermal Model Parameters

DESCRIPTION

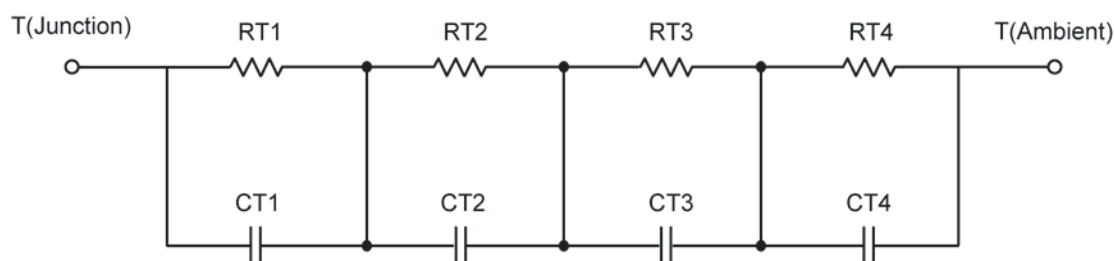
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

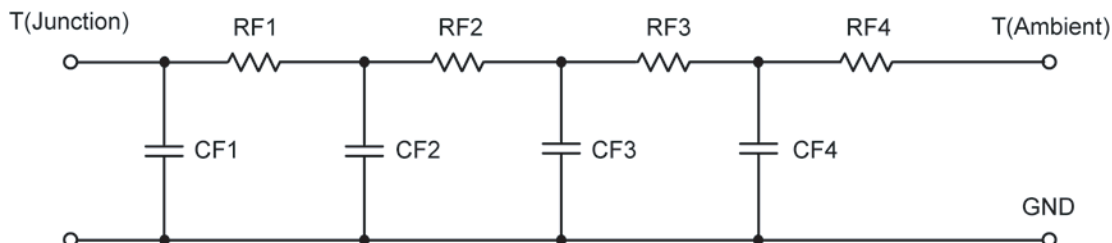
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	5.5372	N/A	13.5384
RT2	27.8770	N/A	3.1354
RT3	20.1395	N/A	8.3301
RT4	56.4463	N/A	14.9961
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	2.3286 m	N/A	7.5561 m
CT2	54.2793 m	N/A	2.0729 m
CT3	12.1622 m	N/A	209.1380 m
CT4	1.3383	N/A	43.9567 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	9.4879	N/A	2.9606
RF2	28.9659	N/A	17.3231
RF3	20.1927	N/A	16.0548
RF4	51.3535	N/A	3.6615
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	2.2280 m	N/A	685.4423 u
CF2	9.6163 m	N/A	5.0699 m
CF3	100.7188 m	N/A	30.9504 m
CF4	1.4247	N/A	727.2935 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya, IEEE / SEMITHERM 2002

